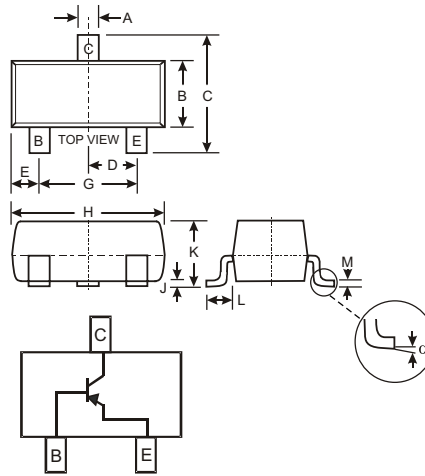


Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (MMBTA05 / MMBTA06)
- Ideal for Medium Power Amplification and Switching

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- MMBTA55 Marking (See Page 2): K2H
- MMBTA56 Marking (See Page 2): K2G
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMBTA55	MMBTA56	Unit
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	V
Emitter-Base Voltage	V_{EBO}	-4.0		V
Collector Current - Continuous (Note 1)	I_C	-500		mA
Power Dissipation (Note 1)	P_d	300		mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417		$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150		$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

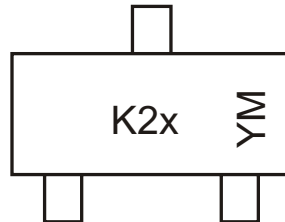
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	MMBTA55 MMBTA56 $V_{(BR)CBO}$	-60 -80	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	MMBTA55 MMBTA56 $V_{(BR)CEO}$	-60 -80	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4.0	—	V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	MMBTA55 MMBTA56 I_{CBO}	—	-100	nA	$V_{CB} = -60\text{V}, I_E = 0$ $V_{CB} = -80\text{V}, I_E = 0$
Collector Cutoff Current	MMBTA55 MMBTA56 I_{CEX}	—	-100	nA	$V_{CE} = -60\text{V}, I_{BO} = 0\text{V}$ $V_{CE} = -80\text{V}, I_{BO} = 0\text{V}$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	100	—	—	$I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25	V	$I_C = -100\text{mA}, I_B = -10\text{mA}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-1.2	V	$I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f_T	50	—	MHz	$V_{CE} = -1.0\text{V}, I_C = -100\text{mA}, f = 100\text{MHz}$

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 3)

Device	Packaging	Shipping
MMBTA55-7 MMBTA56-7	SOT-23	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

K2x = Product Type Marking Code, ex: K2H = MMBTA55
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D